

PN5114 P-CHANNEL JFET



Linear Systems replaces discontinued Siliconix PN5114

This analog switch is designed for inverting switching into inverting input of an Operational Amplifier.

The TO-92 provides a low cost option and ease of manufacturing.

(See Packaging Information).

PN5114 Benefits:

- Low On Resistance
- $I_{D(off)} \le 500 \text{ pA}$
- Switches directly from TTL logic

PN5114 Applications:

- **Analog Switches**
- Commutators
- Choppers

FEATURES					
DIRECT REPLACEMENT FOR SILICONIX PN5114					
LOW ON RESISTANCE	$r_{DS(on)} \le 75\Omega$				
LOW CAPACITANCE 6pF					
ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)					
Maximum Temperatures					
Storage Temperature	-55°C to +200°C				
Operating Junction Temperature -55°C to +200°C					
Maximum Power Dissipation					
Continuous Power Dissipation	500mW				
MAXIMUM CURRENT					
Gate Current (Note 1)	I _G = -50mA				
MAXIMUM VOLTAGES					
Gate to Drain Voltage	V _{GDS} = 30V				
Gate to Source Voltage	V _{GSS} = 30V				

DNE114 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

PNST14 ELECT	RICAL CHARACTERISTICS @ 25°C (unless other)	vise noteuj				
SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_GSS	Gate to Source Breakdown Voltage	30			V	$I_{G} = 1\mu A$, $V_{DS} = 0V$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	4		10		$V_{DS} = -15V, I_{D} = -1nA$
V _{GS(F)}	Gate to Source Forward Voltage		-0.7	-1		$I_G = -1mA$, $V_{DS} = 0V$
V _{DS(on)}			-1.0	-1.3		$V_{GS} = 0V, I_{D} = -15mA$
	Drain to Source On Voltage		-0.7			$V_{GS} = 0V, I_{D} = -7mA$
			-0.5			$V_{GS} = 0V$, $I_D = -3mA$
I _{DSS}	Drain to Source Saturation Current (Note 2)	-30		-90	mA	$V_{DS} = -18V, V_{GS} = 0V$
I _{GSS}	Gate Reverse Current		5	500		$V_{GS} = 20V, \ V_{DS} = 0V$
I _G	Gate Operating Current		-5			$V_{DS} = -15V, I_{D} = -1mA$
		-	-10	-500	pA	$V_{DS} = -15V, V_{GS} = 12V$
I _{D(off)}	Drain Cutoff Current		-10			$V_{DS} = -15V, V_{GS} = 7V$
			-10	-		$V_{DS} = -15V, V_{GS} = 5V$
r _{DS(on)}	Drain to Source On Resistance			75	Ω	$I_{D} = -1 \text{mA}, V_{GS} = 0 \text{V}$

PN5114 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
g fs	Forward Transconductance		4.5		mS	$V_{DS} = -15V, I_D = 1mA, f = 1kHz$
g _{os}	Output Conductance		20		μS	
r _{DS(on)}	Drain to Source On Resistance			75	Ω	$I_D = 0A$, $V_{GS} = 0V$, $f = 1kHz$
C _{iss}	Input Capacitance		20	25		$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$
			5	7	pF	$V_{DS} = 0V, V_{GS} = 12V, f = 1MHz$
C_{rss}	Reverse Transfer Capacitance		6			$V_{DS} = 0V$, $V_{GS} = 7V$, $f = 1MHz$
			6			$V_{DS} = 0V$, $V_{GS} = 5V$, $f = 1MHz$
e _n	Equivalent Noise Voltage		20		nV/√Hz	$V_{DG} = 10V$, $I_D = 10mA$, $f = 1kHz$

PN5114 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

SYM	BOL	CHARACTERISTIC		UNITS	CONDITIONS
t _{d(}	on)	Turn On Time	6		V _{GS} (L) = -11V
t	r	Turn On Rise Time	10	ns	$V_{GS}(H) = 0V$
t _{d(c}	off)	Turn Off Time	6	113	See Switching Circuit
t	f	Turn Off Fall Time	15		

Note 1 - Absolute maximum ratings are limiting values above which PN5114 serviceability may be impaired. Note 2 - Pulse test: PW≤ 300 µs, Duty Cycle ≤ 3%

PN5114 SWITCHING CIRCUIT PARAMETERS

V _{DD}	-10V			
V_{GG}	20V			
R _L	430Ω			
R_{G}	100Ω			
I _{D(on)}	-15mA			

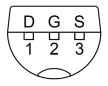
Micross Components Europe

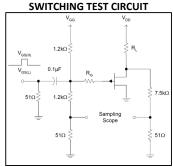
Available Packages:

PN5114 in TO-92 PN5114 in bare die.

Please contact Micross for full package and die dimensions

TO-92 (Bottom View)





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